

40V, 403A, 0.9mΩ N-channel Power SGT MOSFET

JMSL040SPTLQ

Features

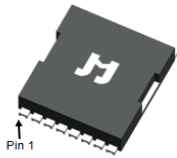
- Ultra-low ON-resistance, $R_{DS(ON)}$
- Low Gate Charge
- 100% UIS Tested
- 100% ΔV_{ds} Tested
- Halogen-free; RoHS-compliant
- AEC-Q101 Qualified

Applications

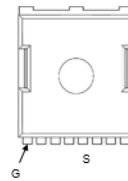
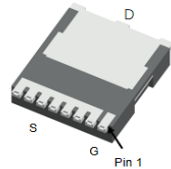
- Load Switch
- PWM Application
- General Automotive Application

Product Summary

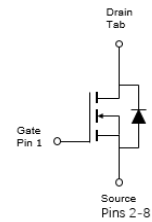
Parameters	Value	Unit
V_{DSS}	40	V
$V_{GS(th)}_{Typ}$	1.5	V
$I_D(@V_{GS}=10V)$	403	A
$R_{DS(ON)}_{Typ}(@V_{GS}=10V)$	0.9	mΩ
$R_{DS(ON)}_{Typ}(@V_{GS}=4.5V)$	1.2	mΩ



PowerJE®10x12



Pin Assignment



Schematic Diagram

Ordering Information

Device	Marking	MSL	Form	Package	Reel(pcs)	Per Carton (pcs)
JMSL040SPTLQ-13	SL040SPQ	1	Tape&Reel	PowerJE®10x12	2000	10000

Absolute Maximum Ratings (@ $T_C = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Unit
V_{DS}	Drain-to-Source Voltage	40	V
V_{GS}	Gate-to-Source Voltage	± 20	V
I_D	Continuous Drain Current	$T_C = 25^\circ\text{C}$	403
		$T_C = 100^\circ\text{C}$	285
I_{DM}	Pulsed Drain Current ⁽¹⁾	Refer to Fig.4	A
E_{AS}	Single Pulsed Avalanche Energy ⁽²⁾	265	mJ
P_D	Power Dissipation	$T_C = 25^\circ\text{C}$	333
		$T_C = 100^\circ\text{C}$	167
T_J, T_{STG}	Junction & Storage Temperature Range	-55 to 175	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Max	Unit
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient ⁽³⁾	39	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance, Junction to Case	0.45	

**Electrical Characteristics** ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$	40	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 32\text{V}, V_{GS} = 0\text{V}$	-	-	1.0	μA
I_{GSS}	Gate-Body Leakage Current	$V_{DS} = 0\text{V}, V_{GS} = \pm 20\text{V}$	-	-	± 100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	1.1	1.5	2.0	V
$R_{DS(ON)}$	Static Drain-Source ON-Resistance ⁽⁴⁾	$V_{GS} = 10\text{V}, I_D = 20\text{A}$	-	0.9	1.2	m Ω
		$V_{GS} = 4.5\text{V}, I_D = 15\text{A}$	-	1.2	1.6	m Ω
Dynamic Characteristics						
R_g	Gate Resistance	$f = 1\text{MHz}$	-	1.2	-	Ω
C_{iss}	Input Capacitance	$V_{GS} = 0\text{V}, V_{DS} = 20\text{V},$ $f = 1\text{MHz}$	5486	7681	10369	pF
C_{oss}	Output Capacitance		2545	3563	4810	pF
C_{riss}	Reverse Transfer Capacitance		171	240	324	pF
Q_g	Total Gate Charge	$V_{GS} = 0 \text{ to } 10\text{V}$ $V_{DS} = 20\text{V}, I_D = 20\text{A}$	88	123	166	nC
Q_{gs}	Gate Source Charge		15	21	28	nC
Q_{gd}	Gate Drain("Miller") Charge		17	24	32	nC
Switching Characteristics						
$t_{d(on)}$	Turn-On DelayTime	$V_{GS} = 10\text{V}, V_{DD} = 20\text{V}$ $I_D = 20\text{A}, R_{GEN} = 3\Omega$	-	17	-	ns
t_r	Turn-On Rise Time		-	36	-	ns
$t_{d(off)}$	Turn-Off DelayTime		-	83	-	ns
t_f	Turn-Off Fall Time		-	40	-	ns
Body Diode Characteristics						
I_S	Maximum Continuous Body Diode Forward Current		-	-	403	A
I_{SM}	Maximum Pulsed Body Diode Forward Current		-	-	1611	A
V_{SD}	Body Diode Forward Voltage	$V_{GS} = 0\text{V}, I_S = 20\text{A}$	-		1.2	V
t_{rr}	Body Diode Reverse Recovery Time	$I_F = 20\text{A}, di/dt = 100\text{A}/\mu\text{s}$	51	72	97	ns
Q_{rr}	Body Diode Reverse Recovery Charge		-	117	-	nC

- Notes:
1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
 2. E_{AS} condition: Starting $T_J = 25^\circ\text{C}$, $V_{DD} = 20\text{V}$, $V_{GS} = 10\text{V}$, $R_G = 25\text{ohm}$, $L = 3\text{mH}$, $I_{AS} = 13.3\text{A}$, $V_{DD} = 0\text{V}$ during time in avalanche.
 3. $R_{\theta JA}$ is measured with the device mounted on a 1inch^2 pad of 2oz copper FR4 PCB.
 4. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 0.5\%$.



Typical Performance Characteristics

Figure 1: Power De-rating

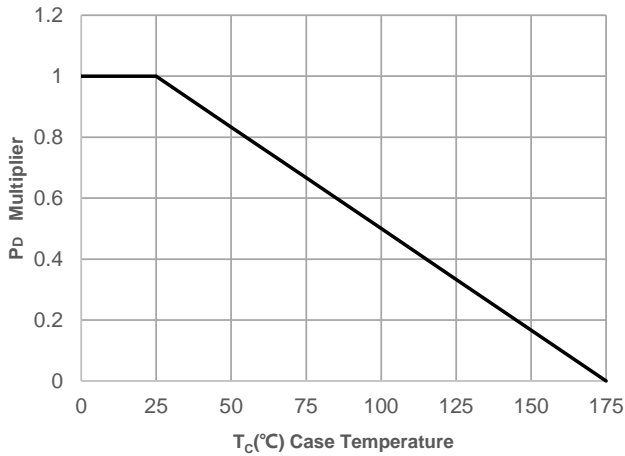


Figure 2: Current De-rating

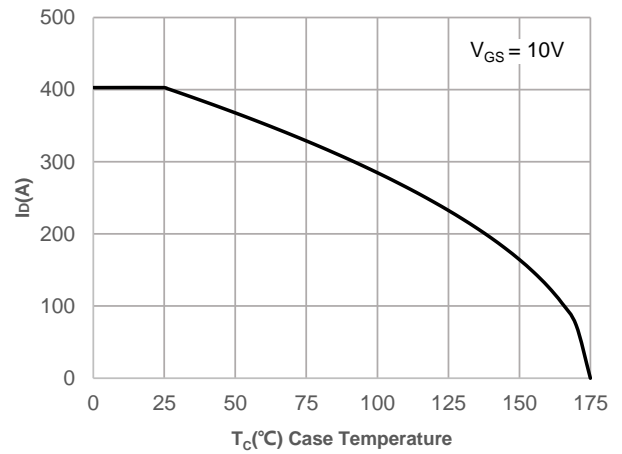


Figure 3: Normalized Maximum Transient Thermal Impedance

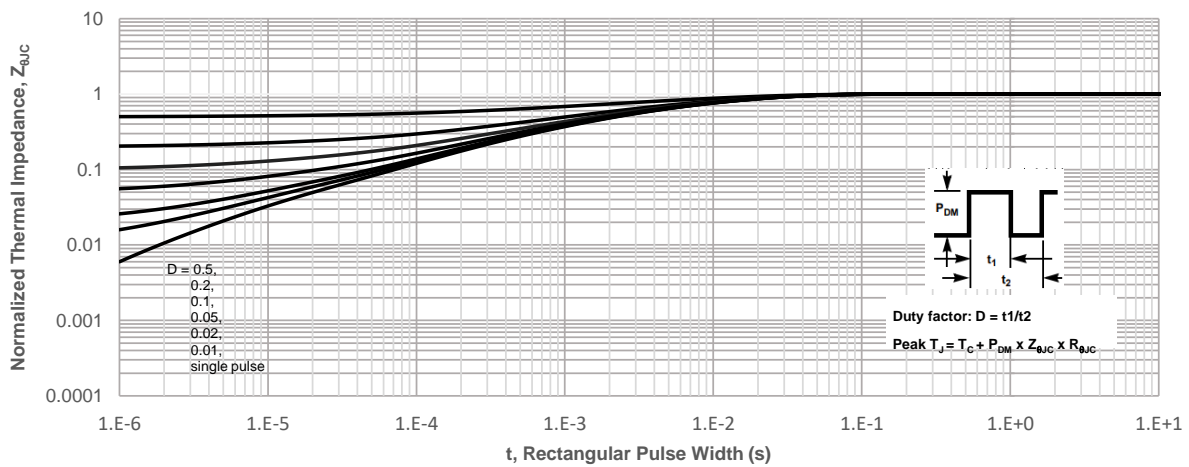
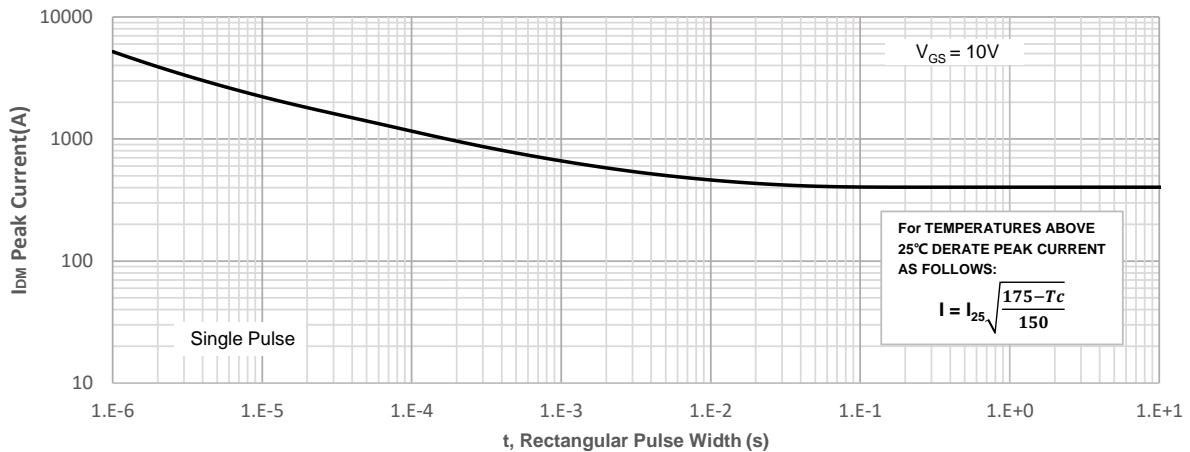
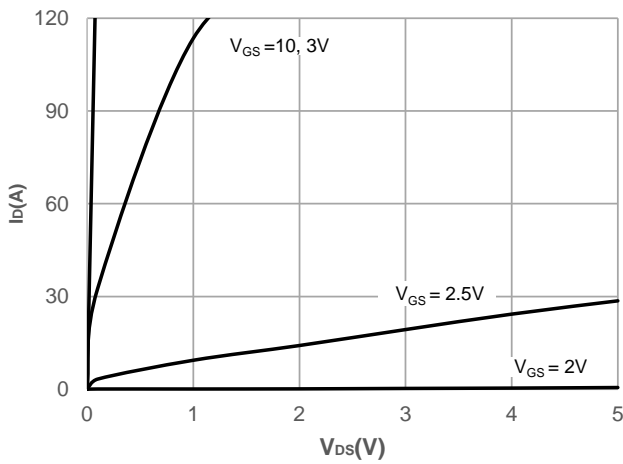
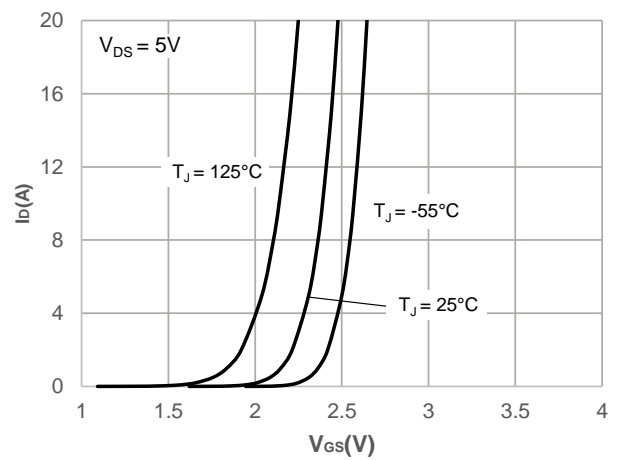
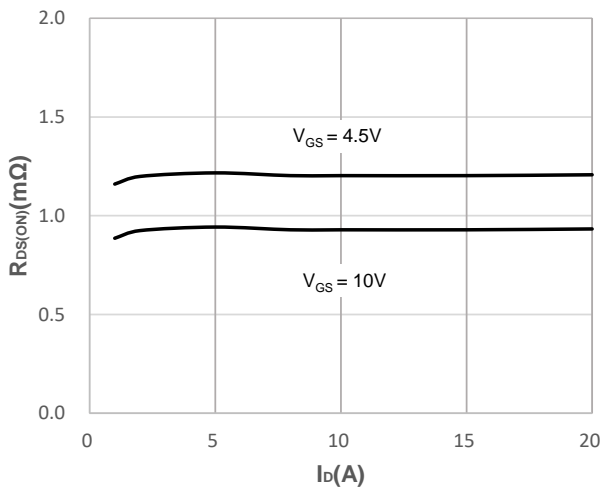
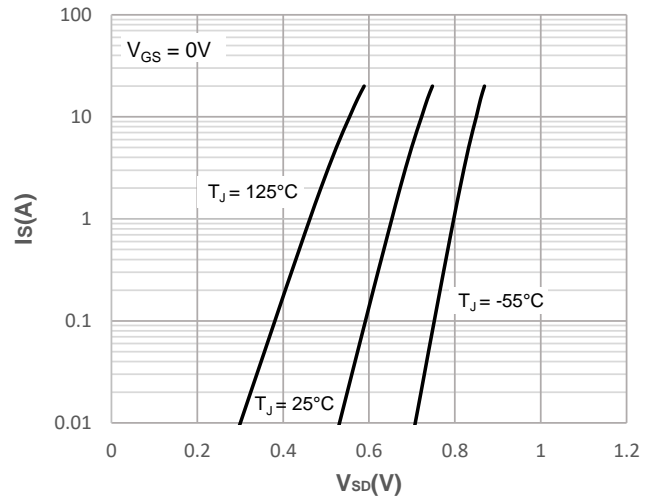
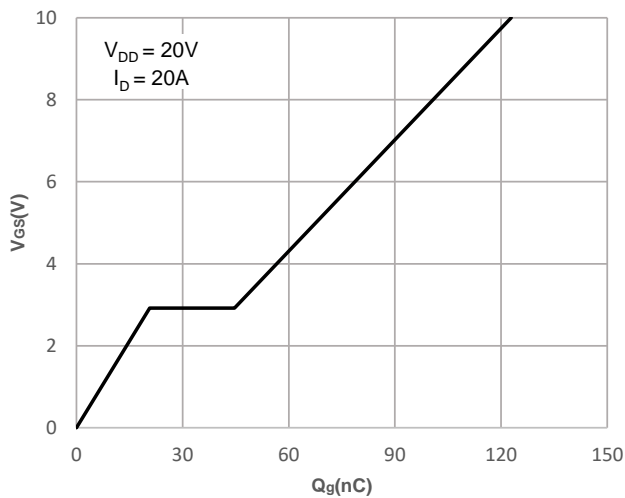
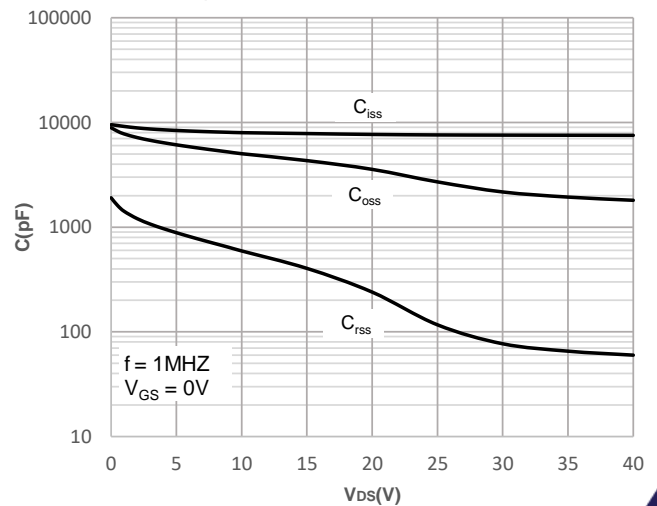


Figure 4: Peak Current Capacity



Typical Performance Characteristics

Figure 5: Output Characteristics

Figure 6: Typical Transfer Characteristics

Figure 7: On-resistance vs. Drain Current

Figure 8: Body Diode Characteristics

Figure 9: Gate Charge Characteristics

Figure 10: Capacitance Characteristics


Typical Performance Characteristics

Figure 11: Normalized Breakdown voltage vs. Junction Temperature

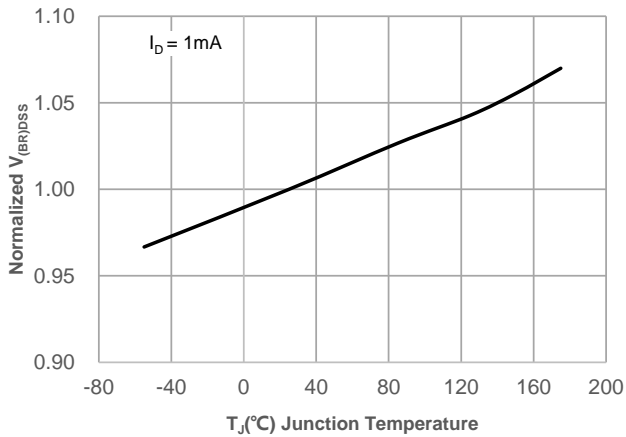


Figure 12: Normalized on Resistance vs. Junction Temperature

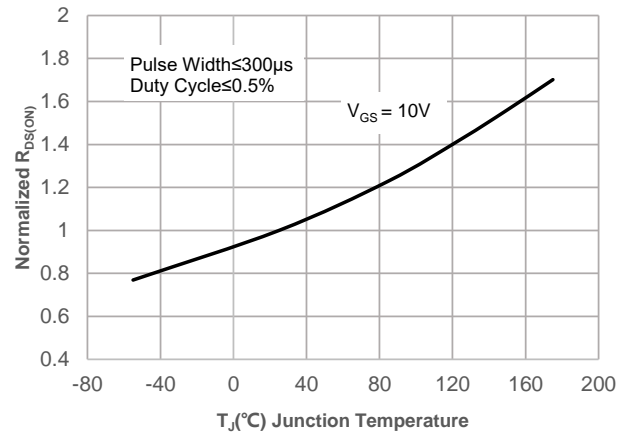


Figure 13: Normalized Threshold Voltage vs. Junction Temperature

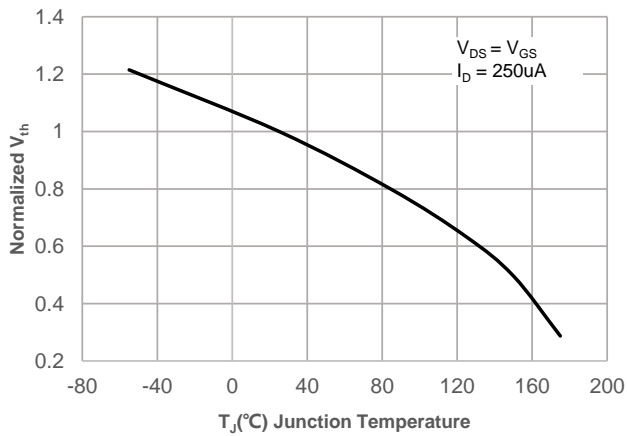


Figure 14: $R_{DS(ON)}$ vs. V_{GS}

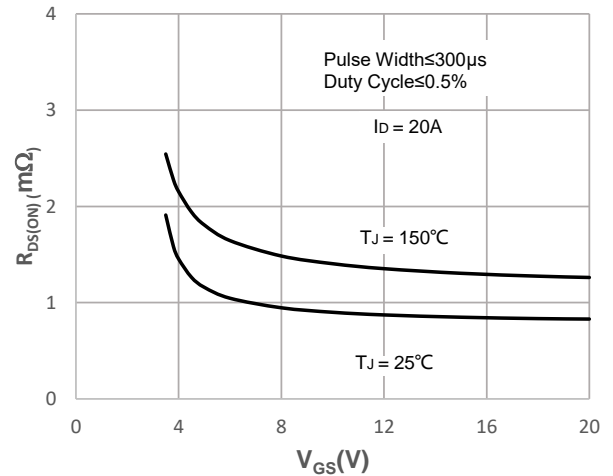
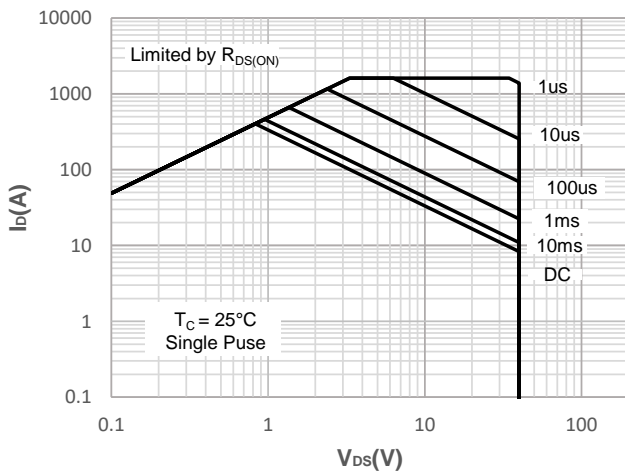


Figure 15: Maximum Safe Operating Area



Test Circuit

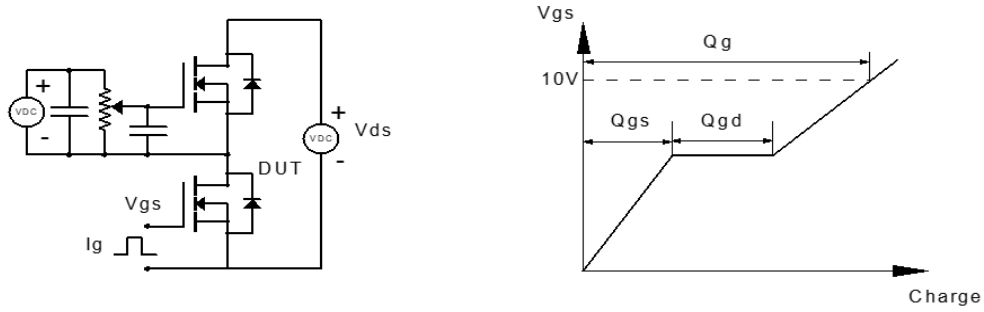


Figure 1: Gate Charge Test Circuit & Waveform

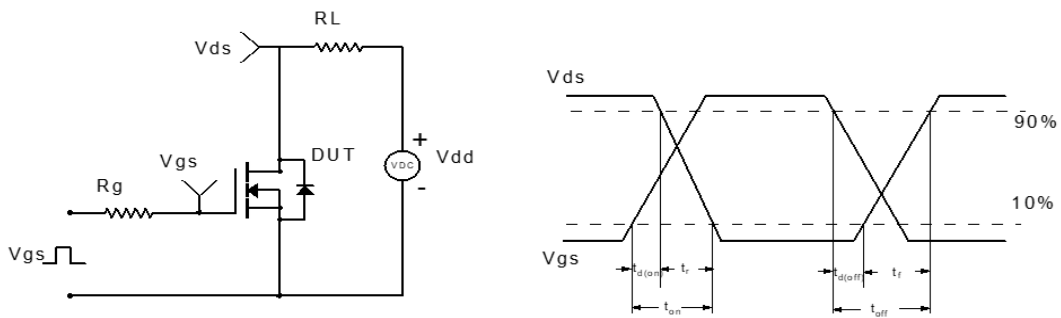


Figure 2: Resistive Switching Test Circuit & Waveform



Figure 3: Unclamped Inductive Switching Test Circuit & Waveform

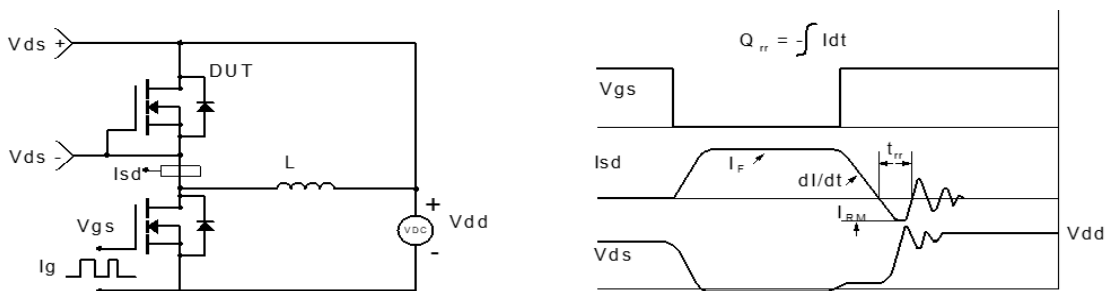
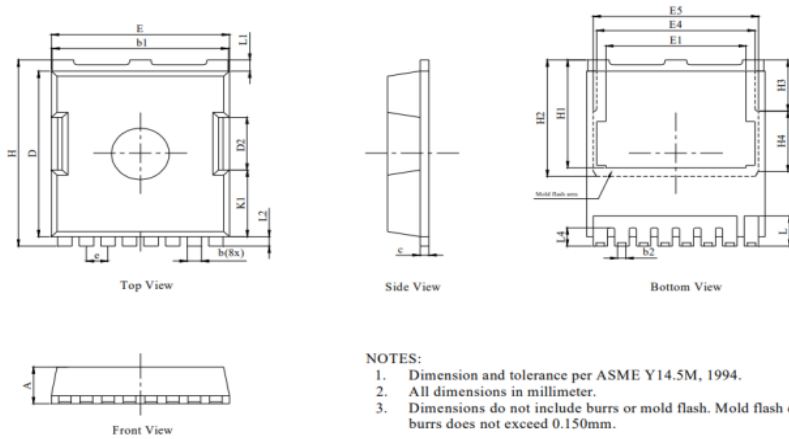


Figure 4: Diode Recovery Test Circuit & Waveform

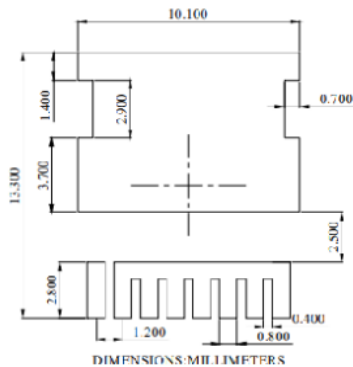
Package Mechanical Data(PowerJE®10x12)

Package Outlines



DIM.	MILLIMETER		
	MIN	NOM	MAX
A	2.20	2.30	2.50
b	0.70	0.80	0.90
b1	9.70	9.80	9.90
b2	0.42	0.46	0.50
C	0.40	0.50	0.65
D	10.28	10.38	10.58
D2	3.30		
E	9.70	9.90	10.10
E1	7.80		
E4	8.80		
E5	9.20		
e	1.20(BSC)		
H	11.48	11.68	11.88
H1	6.55	6.75	6.85
H2	7.30		
H3	3.20		
H4	3.80		
K1	4.18		
L	1.70	1.90	2.10
L1	0.70		
L2	0.60		
L4	1.00	1.15	1.30

Recommended Soldering Footprint



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